

Prof. Ohmi's Paper

January–December, 2013

- E1583 (F) Tomoyuki Suwa, Akinobu Teramoto, Yuki Kumagai, Kenichi Abe, Xiang Li, Yukihiro Nakao, Masashi Yamamoto, Hiroshi Nohira, Takayuki Muro, Toyohiko Kinoshita, Shigetoshi Sugawa, Tadahiro Ohmi, Takeo Hattori, “Chemical Structure of Interfacial Transition Layer Formed on Si(100) and Its Dependence on Oxidation Temperature, Annealing in Forming Gas, and Difference in Oxidizing Species,” Japanese Journal of Applied Physics, Vol.52, 031302, February 2013.
- E1583-2 (C) 諏訪智之、寺本章伸、熊谷勇喜、阿部健一、李翔、中尾幸久、山本雅士、野平博司、室隆桂之、木下豊彦、須川成利、大見忠弘、服部健雄、「Chemical Structure of Interfacial Transition Layer Formed on Si(100) and Its Dependence on Oxidation Temperature, Annealing in Forming Gas, and Difference in Oxidizing Species」、第75回応用物理学会秋季学術講演会(公益社団法人応用物理学会)、応用物理学会優秀論文賞受賞記念講演、19a-17-6、2014年9月。
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- E1586(C) A. Yonezawa, A. Teramoto, T. Obara, R. Kuroda, S. Sugawa and T. Ohmi, “The Study of Time Constant Analysis in Random Telegraph Noise at the Subthreshold Voltage Region,” IEEE International Reliability Physics Symposium 2013, XT.11.1, Monterey, April 2013.
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- E1592 (C) Akinobu Teramoto, Shigetoshi Sugawa, Tadahiro Ohmi, "High-Speed and Highly Accurate Evaluation of Electrical Characteristics in MOSFETs," Proceedings of International Conference on IC Design and Technology 2013, pp.187-190, Invited Paper, Pavia, Italy, May 2013.
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